



F. Silicon and Group-IV Devices and Integration Technology **분과**

2019년 2월 15일(금), 15:30-17:15

Room C (가람홀, 2층)

[FC3-F] Tunnel FETs and NEM Devices

좌장: 김경록 교수(UNIST), 신창환 교수(성균관대학교)

<p>FC3-F-1 15:30-15:45</p>	<p>Measurement Temperature Dependence on the Electrical Characteristics of Si and InGaAs Tunnel FETs Donghwan Lim, Hoonhee Han, and Changhwan Choi <i>Division of Materials Science and Engineering, Hanyang University</i></p>
<p>FC3-F-2 15:45-16:00</p>	<p>Nanoelectromechanical (NEM) Memory Switches with Notched Anchors for Low-Voltage Operation Hyun Chan Jo, Min Hee Kang, and Woo Young Choi <i>Department of Electronic Engineering, Sogang University</i></p>
<p>FC3-F-3 16:00-16:15</p>	<p>Design Guideline of Tunnel FETs (TFETs) Considering Negative Differential Transconductance (NDT) Jang Woo Lee, Min Woo Kang, and Woo Young Choi <i>Department of Electronic Engineering, Sogang University</i></p>
<p>FC3-F-4 16:15-16:30</p>	<p>Demonstration of Ge Condensed SiGe channel Tunnel FETs and Co-integration with CMOS Junil Lee¹, Ryoongbin Lee¹, Sihyun Kim¹, Hyun-Min Kim¹, Kitae Lee¹, Soyoun Kim¹, Munhyeon Kim¹, Yunho Choi¹, Sangwan Kim², and Byung-Gook Park¹ ¹<i>Department of Electrical and Computer Engineering, and ISRC, Seoul National University,</i> ²<i>Department of Electrical and Computer Engineering, Ajou University</i></p>
<p>FC3-F-5 16:30-16:45</p>	<p>Monolithic-3D (M3D) CMOS-nanoelectromechanical (CMOS-NEM) Reconfigurable Logic (RL) Circuits Ji Wang Ko and Woo Young Choi <i>Department of Electronic Engineering, Sogang University</i></p>
<p>FC3-F-6 16:45-17:00</p>	<p>Theoretical Study for Ferroelectric-Gated Nano-Electro-Mechanical Diode Non-Volatile Memory Cell Kihun Choe¹ and Changhwan Shin² ¹<i>Department of Electrical and Computer Engineering, University of Seoul,</i> ²<i>Department of Electrical and Computer Engineering, Sungkyunkwan University</i></p>
<p>FC3-F-7 17:00-17:15</p>	<p>Surrounding Channel Nanowire Tunnel Field-Effect Transistor (SCNW-TFET) with Dual-Gate to Reduce a Hump Phenomenon Seong-Hyun Lee¹, Ye Sung Kwon¹, Jang Hyun Kim², and Sangwan Kim¹ ¹<i>Department of Electrical and Computer Engineering, Ajou University,</i> ²<i>Department of Electrical and Computer Engineering, Seoul National University</i></p>